

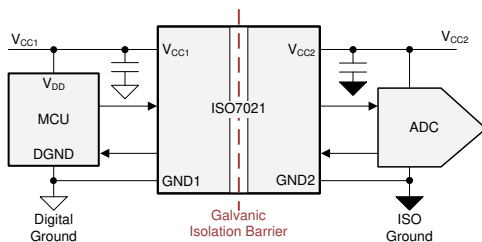
# ISO7021 超低消費電力 2 チャンネル・デジタル・アイソレータ

## 1 特長

- 超低消費電力
  - チャンネルあたり 4.8μA の静止電流 (3.3V)
  - 100kbps 時にチャンネルあたり 15μA (3.3V)
  - 1Mbps 時にチャンネルあたり 120μA (3.3V)
- 堅牢な絶縁バリア
  - 推定寿命: 100 年超
  - 定格絶縁電圧: 3000V<sub>RMS</sub>
  - CMTI: ±100kV/μs (標準値)
- 広い電源電圧範囲: 1.71V ~ 1.89V、2.25V ~ 5.5V
- 広い温度範囲: -55°C ~ +125°C
- 小型の 8-SOIC パッケージ (8-D)
- 信号速度: 最大 4Mbps
- デフォルト出力 HIGH (ISO7021) および LOW (ISO7021F) のオプション
- 堅牢な電磁気互換性 (EMC)
  - システム・レベルの ESD、EFT、サージ耐性
  - 絶縁バリアの両側で ±8kV の IEC 61000-4-2 接触放電保護
  - 超低エミッション
- 安全関連認証 (予定):
  - DIN V VDE 0884-11:2017-01
  - UL 1577 部品認定プログラム
  - IEC 60950-1、IEC 62368-1、IEC 61010-1、IEC60601-1 および GB 4943.1-2011 認証
  - IECEX (IEC 60079-0 & IEC 60079-11) および ATEX (EN IEC60079-0 & EN 60079-11)

## 2 アプリケーション

- 4mA ~ 20mA ループ駆動のフィールド・トランスミッタ
- ファクトリ・オートメーションとプロセス・オートメーション
- 低消費電力 GPIO、UART 絶縁



アプリケーション概略回路図

## 3 概要

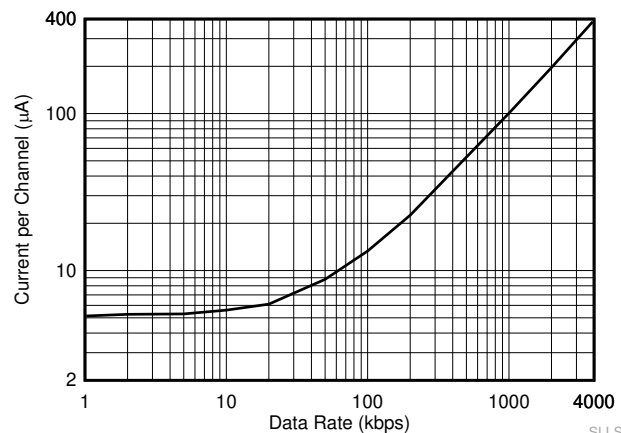
ISO7021 デバイスは超低消費電力の・デジタル・アイソレータで、CMOS または LVCMOS デジタル I/O を絶縁できます。それぞれの絶縁チャンネルにはロジック入力および出力バッファがあり、二重の容量性二酸化ケイ素 (SiO<sub>2</sub>) 絶縁バリアによって分離されています。革新的なエッジ・ベースのアーキテクチャとオン / オフ変調方式の組み合わせにより、超低消費電力でありながら、UL1577 に準拠した 3000V<sub>RMS</sub> の定格絶縁電圧を実現しています。デバイスのチャンネルごとの動的な消費電流は 120μA/Mbps 未満、チャンネルごとの静的な消費電流は 3.3V において 4.8μA なので、ISO7021 は電力と熱の両方において制約のあるシステム設計で使用できます。

このデバイスは最低 1.71V、最高 5.5V で動作し、絶縁バリアの両側の電源電圧が異なる場合も完全に機能します。2 チャンネル・アイソレータは、8 SOIC パッケージに封止された 1 つの順方向チャンネルと 1 つの逆方向チャンネルを備えたナロー・ボディ 8-SOIC パッケージで供給されます。このデバイスには、デフォルト出力が HIGH と LOW のオプションがあります。入力電力または信号が失われた場合、接尾辞 F のない ISO7021 デバイスでは high、接尾辞 F のある ISO7021F デバイスでは low がデフォルト出力です。詳細については、「[デバイスの機能モード](#)」を参照してください。

### 製品情報

部品番号 (1)	パッケージ	本体サイズ (公称)
ISO7021	SOIC (8-D)	4.90mm × 3.91mm

- (1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



3.3V 時のデータ・レートと消費電力との関係



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## 4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

<b>Changes from Revision * (July 2019) to Revision A (October 2019)</b>	<b>Page</b>
• RTM リリース.....	<b>1</b>
<b>Changes from Revision A (October 2019) to Revision B (August 2020)</b>	<b>Page</b>
• 認証の名前を変更し、完了した ATEX 認証を追加し (予定)、記載して、最初のページを更新。.....	<b>1</b>
• Added IECEx and ATEX to Safety-Related Certifications.....	<b>8</b>
• Added セクション 9.1.2 section.....	<b>20</b>
• Updated pin numbers to reflect 8D package .....	<b>21</b>

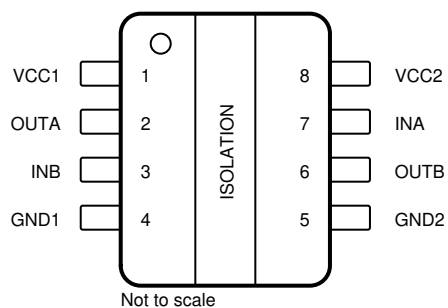
## Device Comparison Table

**表 5-1. Device Features**

PART NUMBER	CHANNEL DIRECTION	MAXIMUM DATA RATE	DEFAULT OUTPUT	PACKAGE	RATED ISOLATION
ISO7021	1 Forward, 1 Reverse	4 Mbps	High	SOIC-8	3000 V <sub>RMS</sub> / 4242 V <sub>PK</sub>
ISO7021 with F suffix	1 Forward, 1 Reverse	4 Mbps	Low	SOIC-8	3000 V <sub>RMS</sub> / 4242 V <sub>PK</sub>

## 5 Pin Configuration and Functions

### Pin Functions



**図 5-1. D Package 8-Pin SOIC Top View**

PIN		I/O	DESCRIPTION
NAME	NO.		
GND1	4	—	Ground connection for V <sub>CC1</sub>
GND2	5	—	Ground connection for V <sub>CC2</sub>
INA	7	I	Input, channel A
INB	3	I	Input, channel B
OUTA	2	O	Output, channel A
OUTB	6	O	Output, channel B
V <sub>CC1</sub>	1	—	Power supply, side 1
V <sub>CC2</sub>	8	—	Power supply, side 2

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1) (2) (3)</sup>

		MIN	MAX	UNIT
Supply Voltage	V <sub>CC1</sub> to GND1	-0.5	6	V
	V <sub>CC2</sub> to GND2	-0.5	6	
Input/Output Voltage	INx to GNDx	-0.5	V <sub>CCX</sub> + 0.5	V
	OUTx to GNDx	-0.5	V <sub>CCX</sub> + 0.5	
Output Current	I <sub>o</sub>	-15	15	mA
Temperature	Operating junction temperature, T <sub>J</sub>		150	°C
	Storage temperature, T <sub>stg</sub>	-65	150	°C

- (1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values except differential I/O bus voltages are with respect to the local ground terminal (GND1 or GND2) and are peak voltage values
- (3) Maximum voltage must not exceed 6 V.

### 6.2 ESD Ratings

<sup>(1) (2)</sup>

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	±6000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup>	±1500	
		Contact discharge per IEC 61000-4-2; Isolation barrier withstand test <sup>(3) (4)</sup>	±8000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.
- (3) IEC ESD strike is applied across the barrier with all pins on each side tied together creating a two-terminal device.
- (4) Testing is carried out in air or oil to determine the intrinsic contact discharge capability of the device.

## 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
$V_{CC1}$ <sup>(1)</sup>	Supply Voltage Side 1	$V_{CCO}$ <sup>(2)</sup> = 1.8 V	1.71		1.89	V
$V_{CC1}$ <sup>(1)</sup>	Supply Voltage Side 1	$V_{CCO}$ = 2.5 V to 5 V	2.25		5.5	V
$V_{CC2}$ <sup>(1)</sup>	Supply Voltage Side 2	$V_{CCO}$ = 1.8 V	1.71		1.89	V
$V_{CC2}$ <sup>(1)</sup>	Supply Voltage Side 2	$V_{CCO}$ = 2.5 V to 5 V	2.25		5.5	V
$V_{IH}$	High level Input voltage		$0.7 \times V_{CCI}$		$V_{CCI}$	V
$V_{IL}$	Low level Input voltage		0		$0.3 \times V_{CCI}$	V
$I_{OH}$	High level output current	$V_{CCO}$ = 5 V	-4			mA
		$V_{CCO}$ = 3.3 V	-2			mA
		$V_{CCO}$ = 2.5 V	-1			mA
		$V_{CCO}$ = 1.8 V	-1			mA
$I_{OL}$	Low level output current	$V_{CCO}$ = 5 V			4	mA
		$V_{CCO}$ = 3.3 V			2	mA
		$V_{CCO}$ = 2.5 V			1	mA
		$V_{CCO}$ = 1.8 V			1	mA
DR	Data Rate		0		4	Mbps
$T_A$	Ambient temperature		-55		125	°C

(1)  $V_{CC1}$  and  $V_{CC2}$  can be set independent of one another

(2)  $V_{CCI}$  = Input-side  $V_{CC}$ ;  $V_{CCO}$  = Output-side  $V_{CC}$

## 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		ISO7021	UNIT
		D (SOIC)	
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	94.3	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	28.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	43.6	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	2.3	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	42.9	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	—	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics application report](#).

## 6.5 Power Ratings

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$P_D$	Maximum power dissipation (both sides)	$V_{CC1} = V_{CC2} = 5.5\text{ V}$ , $T_J = 150^\circ\text{C}$ , $C_L = 15\text{ pF}$ , Input a 2-MHz 50% duty cycle square wave			8.4	mW
$P_{D1}$	Maximum power dissipation (side-1)				4.2	mW
$P_{D2}$	Maximum power dissipation (side-2)				4.2	mW

## 6.6 Insulation Specifications

PARAMETER		TEST CONDITIONS	SPECIFIC ATIONS	UNIT
			8-D	
IEC 60664-1				
CLR	External clearance <sup>(1)</sup>	Side 1 to side 2 distance through air	4	mm
CPG	External creepage <sup>(1)</sup>	Side 1 to side 2 distance across package surface	4	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	>17	μm
CTI	Comparative tracking index	IEC 60112; UL 746A	>600	V
	Material Group	According to IEC 60664-1	I	
	Overvoltage category	Rated mains voltage ≤ 150 V <sub>RMS</sub>	I-IV	
		Rated mains voltage ≤ 300 V <sub>RMS</sub>	I-III	
DIN V VDE V 0884-11:2017-01				
V <sub>IORM</sub>	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	566	V <sub>PK</sub>
V <sub>IOWM</sub>	Maximum isolation working voltage	AC voltage (sine wave); time-dependent dielectric breakdown (TDDb) test;	400	V <sub>RMS</sub>
		DC voltage	566	V <sub>DC</sub>
V <sub>IOTM</sub>	Maximum transient isolation voltage	V <sub>TEST</sub> = V <sub>IOTM</sub> , t = 60 s (qualification); V <sub>TEST</sub> = 1.2 × V <sub>IOTM</sub> , t = 1 s (100% production)	4242	V <sub>PK</sub>
V <sub>IOSM</sub>	Maximum surge isolation voltage <sup>(2)</sup>	Test method per IEC 62368-1, 1.2/50 μs waveform, V <sub>TEST</sub> = 1.6 × V <sub>IOSM</sub> = TBD V <sub>PK</sub> (qualification)	4000	V <sub>PK</sub>
q <sub>pd</sub>	Apparent charge <sup>(3)</sup>	Method a: After I/O safety test subgroup 2/3, V <sub>ini</sub> = V <sub>IOTM</sub> , t <sub>ini</sub> = 60 s; V <sub>pd(m)</sub> = 1.2 × V <sub>IORM</sub> , t <sub>m</sub> = 10 s	≤ 5	pC
		Method a: After environmental tests subgroup 1, V <sub>ini</sub> = V <sub>IOTM</sub> , t <sub>ini</sub> = 60 s; V <sub>pd(m)</sub> = 1.6 × V <sub>IORM</sub> , t <sub>m</sub> = 10 s	≤ 5	
		Method b1: At routine test (100% production) and preconditioning (type test), V <sub>ini</sub> = V <sub>IOTM</sub> , t <sub>ini</sub> = 1 s; V <sub>pd(m)</sub> = 1.875 × V <sub>IORM</sub> , t <sub>m</sub> = 1 s	≤ 5	
C <sub>IO</sub>	Barrier capacitance, input to output <sup>(4)</sup>	V <sub>IO</sub> = 0.4 × sin (2 πft), f = 1 MHz	1	pF
R <sub>IO</sub>	Insulation resistance, input to output <sup>(4)</sup>	V <sub>IO</sub> = 500 V, T <sub>A</sub> = 25°C	> 10 <sup>12</sup>	Ω
		V <sub>IO</sub> = 500 V, 100°C ≤ T <sub>A</sub> ≤ 150°C	> 10 <sup>11</sup>	
		V <sub>IO</sub> = 500 V at T <sub>S</sub> = 150°C	> 10 <sup>9</sup>	
	Pollution degree		2	
	Climatic category		55/125/21	
UL 1577				
V <sub>ISO</sub>	Withstand isolation voltage	V <sub>TEST</sub> = V <sub>ISO</sub> , t = 60 s (qualification); V <sub>TEST</sub> = 1.2 × V <sub>ISO</sub> , t = 1 s (100% production)	3000	V <sub>RMS</sub>

- (1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves, ribs, or both on a printed circuit board are used to help increase these specifications.
- (2) Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.
- (3) Apparent charge is electrical discharge caused by a partial discharge (pd).
- (4) All pins on each side of the barrier tied together creating a two-pin device.

## 6.7 Safety-Related Certifications

VDE	CSA	UL	CQC	TUV	IECEX / ATEX
Plan to certify according to DIN V VDE V 0884-11:2017-01	Certified according to IEC 60950-1 and IEC 62368-1	Plan to certify according to UL 1577 Component Recognition Program	Plan to certify according to GB4943.1-2011	Plan to certify according to EN 61010-1:2010 (3rd Ed) and EN 60950-1:2006/A2:2013	Certified for use in intrinsic safety (IS) to IS applications under ATEX and IECEx.
Maximum transient isolation voltage, 4242 V <sub>PK</sub> ; Maximum repetitive peak isolation voltage, 566 V <sub>PK</sub> ; Maximum surge isolation voltage, 4000 V <sub>PK</sub>	3000 V <sub>RMS</sub> insulation per CSA 60950-1-07+A1+A2, IEC 60950-1 2nd Ed.+A1+A2, CSA 62368-1-14 and IEC 62368-1:2014 370 V <sub>RMS</sub> (DBQ-16) maximum working voltage (pollution degree 2, material group I)	Single protection, 3000 V <sub>RMS</sub>	Basic insulation, Altitude ≤ 5000 m, Tropical Climate, 250 V <sub>RMS</sub> maximum working voltage	3000 V <sub>RMS</sub> insulation per EN 61010-1:2010 (3rd Ed) up to working voltage of 300 V <sub>RMS</sub> 3000 V <sub>RMS</sub> insulation per EN 60950-1:2006/A2:2013 up to working voltage of 370 V <sub>RMS</sub>	ATEX: EN IEC60079-0:2018 and EN 60079-11:2012 IECEX: IEC 60079-0:2017 (7th Ed) and IEC60079-11:2011 (6th Ed) Markings: II 1G Ex ia IIC Ga See the <a href="#">セクション 9.1.2</a>
Certificate planned	Certificate planned	Certificate planned	Certificate planned	Certificate planned	IECEX certificate: IECEx CSA 20.012U ATEX certificate: CSANe 20ATEX2090U

## 6.8 Safety Limiting Values

Safety limiting<sup>(1)</sup> intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>D-8 PACKAGE</b>						
I <sub>S</sub>	Safety input, output, or supply current	R <sub>θJA</sub> = 94.3°C/W, V <sub>I</sub> = 5.5 V, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C			241	mA
		R <sub>θJA</sub> = 94.3°C/W, V <sub>I</sub> = 3.6 V, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C			368	mA
		R <sub>θJA</sub> = 94.3°C/W, V <sub>I</sub> = 2.75 V, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C			482	
		R <sub>θJA</sub> = 94.3°C/W, V <sub>I</sub> = 1.89 V, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C			701	mA
P <sub>S</sub>	Safety input, output, or total power	R <sub>θJA</sub> = 94.3°C/W, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C			1325	mW
T <sub>S</sub>	Maximum safety temperature				150	°C

- (1) The maximum safety temperature, T<sub>S</sub>, has the same value as the maximum junction temperature, T<sub>J</sub>, specified for the device. The I<sub>S</sub> and P<sub>S</sub> parameters represent the safety current and safety power respectively. The maximum limits of I<sub>S</sub> and P<sub>S</sub> should not be exceeded. These limits vary with the ambient temperature, T<sub>A</sub>.  
The junction-to-air thermal resistance, R<sub>θJA</sub>, in the table is that of a device installed on a high-K test board for leaded surface-mount packages. Use these equations to calculate the value for each parameter:  
T<sub>J</sub> = T<sub>A</sub> + R<sub>θJA</sub> × P, where P is the power dissipated in the device.  
T<sub>J(max)</sub> = T<sub>S</sub> = T<sub>A</sub> + R<sub>θJA</sub> × P<sub>S</sub>, where T<sub>J(max)</sub> is the maximum allowed junction temperature.  
P<sub>S</sub> = I<sub>S</sub> × V<sub>I</sub>, where V<sub>I</sub> is the maximum input voltage.



## 6.9 Electrical Characteristics 5V Supply

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{IT+(IN)}$	Rising input switching threshold				$0.7 \times V_{CCI}^{(1)}$	V
$V_{IT-(IN)}$	Falling input switching threshold		$0.3 \times V_{CCI}$			V
$V_{OH}$	High-level output voltage	$I_{OH} = -4 \text{ mA}$	$V_{CCO} - 0.4$			V
$V_{OL}$	Low-level output voltage	$I_{OL} = 4 \text{ mA}$			0.4	V
$V_{I(HYS)}$	Input threshold voltage hysteresis		$0.1 \times V_{CCI}$			V
$I_{IH}$	High-level input current	$V_{IH} = V_{CCI}^{(1)}$ at INx			1	$\mu\text{A}$
$I_{IL}$	Low-level input current	$V_{IL} = 0 \text{ V}$ at INx	-1			$\mu\text{A}$
CMTI	Common mode transient immunity	$V_I = V_{CC}$ or 0 V, $V_{CM} = 1200 \text{ V}$	50	100		kV/us
$C_i$	Input Capacitance <sup>(2)</sup>	$V_I = V_{CC}/2 + 0.4 \times \sin(2\pi f t)$ , $f = 2 \text{ MHz}$ , $V_{CC} = 5 \text{ V}$		2		pF

(1)  $V_{CCI}$  = Input-side  $V_{CC}$ ;  $V_{CCO}$  = Output-side  $V_{CC}$

(2) Measured from input pin to same side ground.

## 6.10 Supply Current Characteristics 5V Supply

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	SUPPLY CURRENT	MIN	TYP	MAX	UNIT
<b>ISO7021</b>						
Supply current - DC signal	$V_I = V_{CC1}$ (ISO7021); $V_I = 0 \text{ V}$ (ISO7021 with F suffix)	$I_{CC1}$		5.9	11.8	$\mu\text{A}$
		$I_{CC2}$		5.9	11.8	$\mu\text{A}$
	$V_I = 0 \text{ V}$ (ISO7021); $V_I = V_{CC1}$ (ISO7021 with F suffix)	$I_{CC1}$		6.5	11.9	$\mu\text{A}$
		$I_{CC2}$		6.5	11.9	$\mu\text{A}$
Supply current - AC signal	10 kbps, No Load	$I_{CC1}$		7.2	12.2	$\mu\text{A}$
		$I_{CC2}$		7.2	12.2	$\mu\text{A}$
	100 kbps, No Load	$I_{CC1}$		15.9	27.7	$\mu\text{A}$
		$I_{CC2}$		15.9	27.7	$\mu\text{A}$
	1 Mbps, No Load	$I_{CC1}$		129.0	175.0	$\mu\text{A}$
		$I_{CC2}$		129.0	175.0	$\mu\text{A}$
Total Supply Current Per Channel	$V_I = V_{CC1}$ (ISO7021); $V_I = 0 \text{ V}$ (ISO7021 with F suffix)	$I_{CC1(ch)} + I_{CC2(ch)}$		5.9	11.4	$\mu\text{A}$
	$V_I = 0 \text{ V}$ (ISO7021); $V_I = V_{CC1}$ (ISO7021 with F suffix)	$I_{CC1(ch)} + I_{CC2(ch)}$		6.5	11.8	$\mu\text{A}$
	10 kbps, No Load	$I_{CC1(ch)} + I_{CC2(ch)}$		7.2	12.2	$\mu\text{A}$
	100 kbps, No Load	$I_{CC1(ch)} + I_{CC2(ch)}$		15.9	27.8	$\mu\text{A}$
	1 Mbps, No Load	$I_{CC1(ch)} + I_{CC2(ch)}$		129.0	175.0	$\mu\text{A}$

## 6.11 Electrical Characteristics 3.3V Supply

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{IT+(IN)}$	Rising input switching threshold				$0.7 \times V_{CCI}^{(1)}$	V
$V_{IT-(IN)}$	Falling input switching threshold		$0.3 \times V_{CCI}$			V
$V_{OH}$	High-level output voltage	$I_{OH} = -2\text{mA}$	$V_{CCO} - 0.3$			V
$V_{OL}$	Low-level output voltage	$I_{OL} = 2\text{mA}$			0.3	V
$V_{I(HYS)}$	Input threshold voltage hysteresis		$0.1 \times V_{CCI}$			V
$I_{IH}$	High-level input current	$V_{IH} = V_{CCI}^{(1)}$ at INx			1	$\mu\text{A}$
$I_{IL}$	Low-level input current	$V_{IL} = 0\text{ V}$ at INx	-1			$\mu\text{A}$
CMTI	Common mode transient immunity	$V_I = V_{CC}$ or 0 V, $V_{CM} = 1200\text{ V}$	50	100		kV/us
$C_i$	Input Capacitance <sup>(2)</sup>	$V_I = V_{CC}/2 + 0.4 \times \sin(2\pi f t)$ , $f = 2\text{ MHz}$ , $V_{CC} = 3.3\text{ V}$		2		pF

(1)  $V_{CCI}$  = Input-side  $V_{CC}$ ;  $V_{CCO}$  = Output-side  $V_{CC}$

(2) Measured from input pin to same side ground.

## 6.12 Supply Current Characteristics 3.3V Supply

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	SUPPLY CURRENT	MIN	TYP	MAX	UNIT
<b>ISO7021</b>						
Supply current - DC signal	$V_I = V_{CC1}$ (ISO7021); $V_I = 0\text{ V}$ (ISO7021 with F suffix)	$I_{CC1}$		4.8	7.8	$\mu\text{A}$
		$I_{CC2}$		4.8	7.8	$\mu\text{A}$
	$V_I = 0\text{ V}$ (ISO7021); $V_I = V_{CC1}$ (ISO7021 with F suffix)	$I_{CC1}$		5.2	8.4	$\mu\text{A}$
		$I_{CC2}$		5.2	8.4	$\mu\text{A}$
Supply current - AC signal	10 kbps, No Load	$I_{CC1}$		5.7	8.8	$\mu\text{A}$
		$I_{CC2}$		5.7	8.8	$\mu\text{A}$
	100 kbps, No Load	$I_{CC1}$		15.0	23.0	$\mu\text{A}$
		$I_{CC2}$		15.0	23.0	$\mu\text{A}$
	1 Mbps, No Load	$I_{CC1}$		120.0	153.0	$\mu\text{A}$
		$I_{CC2}$		120.0	155.0	$\mu\text{A}$
Total Supply Current Per Channel	$V_I = V_{CC1}$ (ISO7021); $V_I = 0\text{ V}$ (ISO7021 with F suffix)	$I_{CC1(ch)} + I_{CC2(ch)}$		4.8	7.8	$\mu\text{A}$
		$I_{CC1(ch)} + I_{CC2(ch)}$		5.2	8.4	$\mu\text{A}$
	10 kbps, No Load	$I_{CC1(ch)} + I_{CC2(ch)}$		5.7	8.8	$\mu\text{A}$
		$I_{CC1(ch)} + I_{CC2(ch)}$		15.0	23.0	$\mu\text{A}$
	100 kbps, No Load	$I_{CC1(ch)} + I_{CC2(ch)}$		15.0	23.0	$\mu\text{A}$
		$I_{CC1(ch)} + I_{CC2(ch)}$		120.0	153.0	$\mu\text{A}$

## 6.13 Electrical Characteristics 2.5V Supply

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{IT+(IN)}$	Rising input switching threshold			$0.7 \times V_{CCI}^{(1)}$	V
$V_{IT-(IN)}$	Falling input switching threshold			$0.3 \times V_{CCI}$	V
$V_{OH}$	High-level output voltage	$I_{OH} = -1\text{mA}$		$V_{CCO} - 0.2$	V
$V_{OL}$	Low-level output voltage	$I_{OL} = 1\text{mA}$		0.2	V
$V_{I(HYS)}$	Input threshold voltage hysteresis			$0.1 \times V_{CCI}$	V
$I_{IH}$	High-level input current	$V_{IH} = V_{CCI}^{(1)}$ at INx		1	$\mu\text{A}$
$I_{IL}$	Low-level input current	$V_{IL} = 0\text{ V}$ at INx	-1		$\mu\text{A}$
CMTI	Common mode transient immunity	$V_I = V_{CC}$ or 0 V, $V_{CM} = 1200\text{ V}$	50	100	kV/us
$C_i$	Input Capacitance <sup>(2)</sup>	$V_I = V_{CC}/2 + 0.4 \times \sin(2\pi f t)$ , $f = 2\text{ MHz}$ , $V_{CC} = 2.5\text{ V}$	2		pF

(1)  $V_{CCI}$  = Input-side  $V_{CC}$ ;  $V_{CCO}$  = Output-side  $V_{CC}$

(2) Measured from input pin to same side ground.

## 6.14 Supply Current Characteristics 2.5V Supply

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	SUPPLY CURRENT	MIN	TYP	MAX	UNIT
<b>ISO7021</b>						
Supply current - DC signal	$V_I = V_{CC1}$ (ISO7021); $V_I = 0\text{ V}$ (ISO7021 with F suffix)	$I_{CC1}$		4.4	6.9	$\mu\text{A}$
		$I_{CC2}$		4.3	6.9	$\mu\text{A}$
	$V_I = 0\text{ V}$ (ISO7021); $V_I = V_{CC1}$ (ISO7021 with F suffix)	$I_{CC1}$		4.8	7.4	$\mu\text{A}$
		$I_{CC2}$		4.8	7.4	$\mu\text{A}$
Supply current - AC signal	10 kbps, No Load	$I_{CC1}$		5.0	7.8	$\mu\text{A}$
		$I_{CC2}$		5.0	7.8	$\mu\text{A}$
	100 kbps, No Load	$I_{CC1}$		12.4	21.2	$\mu\text{A}$
		$I_{CC2}$		12.4	21.2	$\mu\text{A}$
	1 Mbps, No Load	$I_{CC1}$		112.0	144.0	$\mu\text{A}$
		$I_{CC2}$		113.0	144.0	$\mu\text{A}$
Total Supply Current Per Channel	$V_I = V_{CC1}$ (ISO7021); $V_I = 0\text{ V}$ (ISO7021 with F suffix)	$I_{CC1(ch)} + I_{CC2(ch)}$		4.4	6.9	$\mu\text{A}$
		$I_{CC1(ch)} + I_{CC2(ch)}$		4.8	7.4	$\mu\text{A}$
	10 kbps, No Load	$I_{CC1(ch)} + I_{CC2(ch)}$		5.0	7.8	$\mu\text{A}$
		$I_{CC1(ch)} + I_{CC2(ch)}$		12.4	21.2	$\mu\text{A}$
	1 Mbps, No Load	$I_{CC1(ch)} + I_{CC2(ch)}$		113.0	144.0	$\mu\text{A}$
		$I_{CC1(ch)} + I_{CC2(ch)}$		113.0	144.0	$\mu\text{A}$

## 6.15 Electrical Characteristics 1.8V Supply

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{IT+(IN)}$	Rising input switching threshold				$0.7 \times V_{CCI}^{(1)}$	V
$V_{IT-(IN)}$	Falling input switching threshold		$0.3 \times V_{CCI}$			V
$V_{OH}$	High-level output voltage	$I_{OH} = -1\text{mA}$	$V_{CCO} - 0.2$			V
$V_{OL}$	Low-level output voltage	$I_{OL} = 1\text{mA}$			0.2	V
$V_{I(HYS)}$	Input threshold voltage hysteresis		$0.1 \times V_{CCI}$			V
$I_{IH}$	High-level input current	$V_{IH} = V_{CCI}^{(1)}$ at INx			1	$\mu\text{A}$
$I_{IL}$	Low-level input current	$V_{IL} = 0\text{ V}$ at INx	-1			$\mu\text{A}$
CMTI	Common mode transient immunity	$V_I = V_{CC}$ or 0 V, $V_{CM} = 1200\text{ V}$	50	100		kV/us
$C_i$	Input Capacitance <sup>(2)</sup>	$V_I = V_{CC}/2 + 0.4 \times \sin(2\pi ft)$ , $f = 2\text{ MHz}$ , $V_{CC} = 1.8\text{ V}$		2		pF

(1)  $V_{CCI}$  = Input-side  $V_{CC}$ ;  $V_{CCO}$  = Output-side  $V_{CC}$

(2) Measured from input pin to same side ground.

## 6.16 Supply Current Characteristics 1.8V Supply

over operating free-air temperature range (unless otherwise noted)

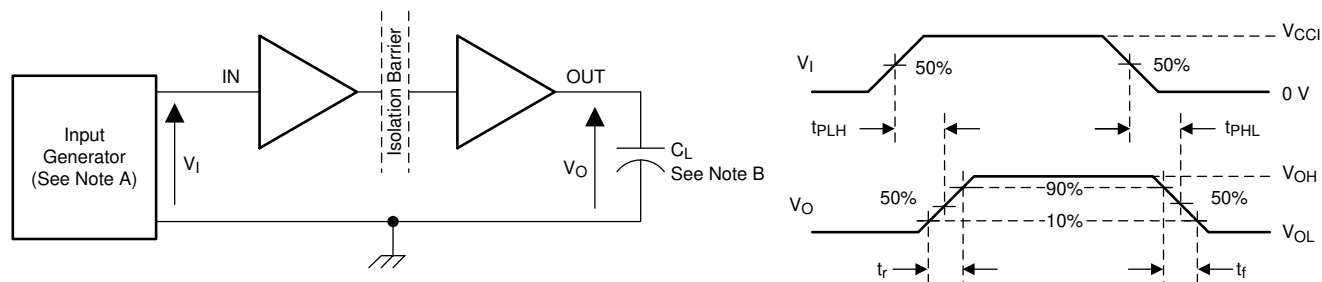
PARAMETER	TEST CONDITIONS	SUPPLY CURRENT	MIN	TYP	MAX	UNIT
<b>ISO7021</b>						
Supply current - DC signal	$V_I = V_{CC1}$ (ISO7021); $V_I = 0\text{ V}$ (ISO7021 with F suffix)	$I_{CC1}$		3.4	5.7	$\mu\text{A}$
		$I_{CC2}$		3.4	5.7	$\mu\text{A}$
	$V_I = 0\text{ V}$ (ISO7021); $V_I = V_{CC1}$ (ISO7021 with F suffix)	$I_{CC1}$		3.8	6.2	$\mu\text{A}$
		$I_{CC2}$		3.8	6.2	$\mu\text{A}$
Supply current - AC signal	10 kbps, No Load	$I_{CC1}$		4.1	6.7	$\mu\text{A}$
		$I_{CC2}$		4.1	6.7	$\mu\text{A}$
	100 kbps, No Load	$I_{CC1}$		9.9	19.3	$\mu\text{A}$
		$I_{CC2}$		9.9	19.3	$\mu\text{A}$
	1 Mbps, No Load	$I_{CC1}$		90.0	134.0	$\mu\text{A}$
		$I_{CC2}$		90.0	134.0	$\mu\text{A}$
Total Supply Current Per Channel	$V_I = V_{CC1}$ (ISO7021); $V_I = 0\text{ V}$ (ISO7021 with F suffix)	$I_{CC1(ch)} + I_{CC2(ch)}$		3.4	5.7	$\mu\text{A}$
	$V_I = 0\text{ V}$ (ISO7021); $V_I = V_{CC1}$ (ISO7021 with F suffix)	$I_{CC1(ch)} + I_{CC2(ch)}$		3.8	6.2	$\mu\text{A}$
	10 kbps, No Load	$I_{CC1(ch)} + I_{CC2(ch)}$		3.9	6.7	$\mu\text{A}$
	100 kbps, No Load	$I_{CC1(ch)} + I_{CC2(ch)}$		9.9	19.3	$\mu\text{A}$
	1 Mbps, No Load	$I_{CC1(ch)} + I_{CC2(ch)}$		90.0	134.0	$\mu\text{A}$
		$I_{CC1(ch)} + I_{CC2(ch)}$				

## 6.17 Switching Characteristics

$V_{CC1}, V_{CC2} = 1.71\text{ V to }1.89\text{ V or }2.25\text{ V to }5.5\text{ V}$  (over recommended operating conditions unless otherwise noted)

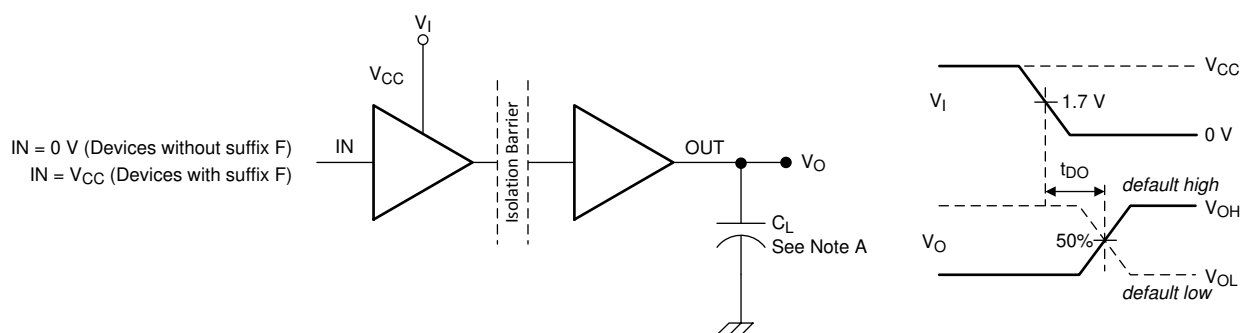
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{PLH}, t_{PHL}$	Propagation delay time	See <a href="#">7-1</a>		140	165	ns
$t_{P(dft)}$	Propagation delay drift			15		ps/°C
$t_{UI}$	Minimum pulse width	See <a href="#">7-1</a>	250			ns
PWD	Pulse width distortion				10	ns
$t_{sk(o)}$	Channel to channel output skew time				10	ns
$t_{sk(p-p)}$	Part to part skew time				70	ns
$t_r$	Output signal rise time	$V_{CC} = 1.71\text{ V to }1.9\text{ V}$ , See <a href="#">7-1</a>			8	ns
		$V_{CC} = 2.25\text{ V to }5.5\text{ V}$ , See <a href="#">7-1</a>			5	ns
$t_f$	Output signal fall time	$V_{CC} = 1.71\text{ V to }1.9\text{ V}$ , See <a href="#">7-1</a>			8	ns
		$V_{CC} = 2.25\text{ V to }5.5\text{ V}$ , See <a href="#">7-1</a>			5	ns
$t_{DO}$	Default output delay time from input power loss	See <a href="#">7-2</a>		400	750	us
$t_{PU}$	Time from UVLO to valid output data		1		5	ms
$F_R$	Refresh rate		5	10		kbps

## 7 Parameter Measurement Information



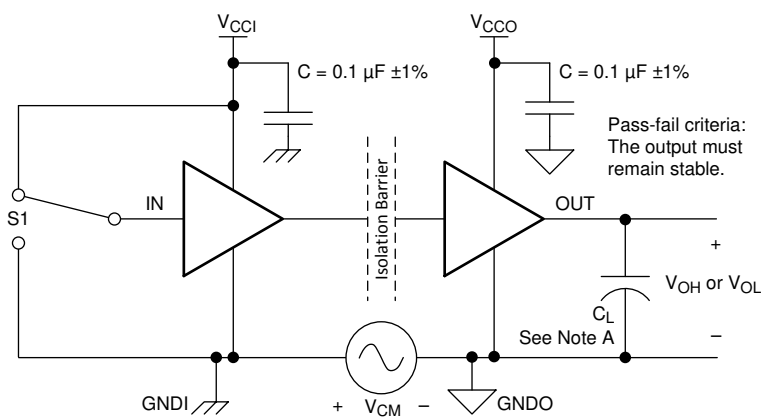
- A. The input pulse is supplied by a generator having the following characteristics:  $\text{PRR} \leq 50 \text{ kHz}$ , 50% duty cycle,  $t_r \leq 3 \text{ ns}$ ,  $t_f \leq 3 \text{ ns}$ ,  $Z_O = 50 \Omega$ . At the input,  $50 \Omega$  resistor is required to terminate Input Generator signal. It is not needed in actual application.
- B.  $C_L = 15 \text{ pF}$  and includes instrumentation and fixture capacitance within  $\pm 20\%$ .

**Figure 7-1. Switching Characteristics Test Circuit and Voltage Waveforms**



- A.  $C_L = 15 \text{ pF}$  and includes instrumentation and fixture capacitance within  $\pm 20\%$ .
- B. Power Supply Ramp Rate =  $10 \text{ mV/ns}$

**Figure 7-2. Default Output Delay Time Test Circuit and Voltage Waveforms**



- A.  $C_L = 15 \text{ pF}$  and includes instrumentation and fixture capacitance within  $\pm 20\%$ .

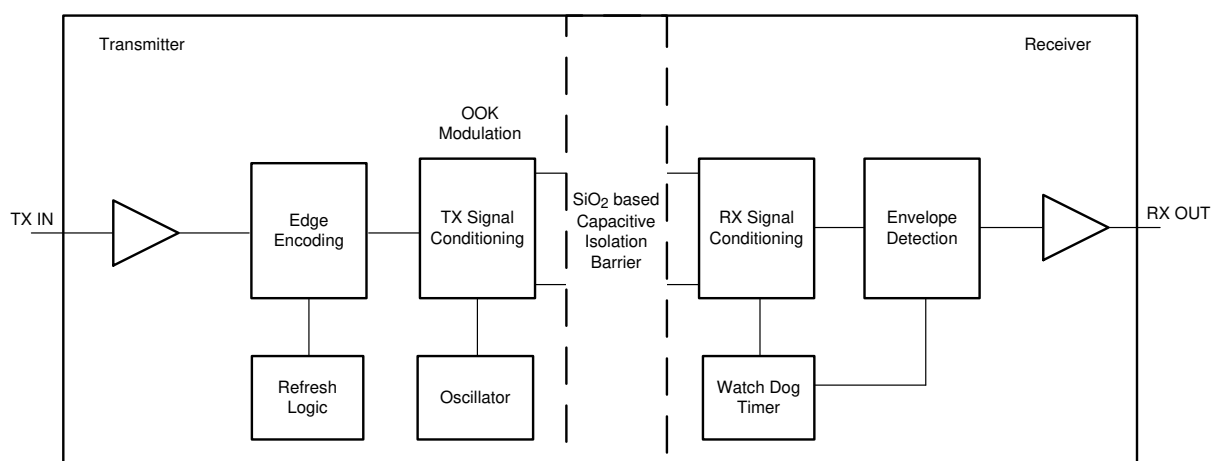
**Figure 7-3. Common-Mode Transient Immunity Test Circuit**

## 8 Detailed Description

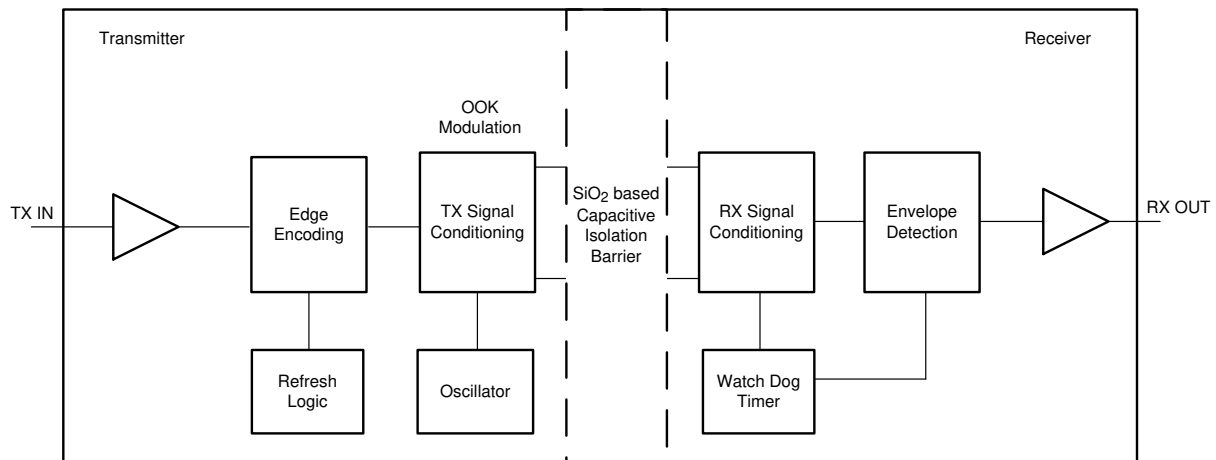
### 8.1 Overview

The ISO7021 device uses edge encoding of data with an ON-OFF keying (OOK) modulation scheme to transmit the digital data across a silicon dioxide isolation barrier. The transmitter uses a high frequency carrier signal to pass data across the barrier representing a signal edge transition. Using this method achieves very low power consumption and high immunity. The receiver demodulates the carrier signal after advanced signal conditioning and produces the output through a buffer stage. For low data rates, a refresh logic option is available to make sure the output state matches the input state. Advanced circuit techniques are used to maximize the CMTI performance and minimize the radiated emissions due to the high frequency carrier and IO buffer switching. The conceptual block diagram of a digital capacitive isolator, [Figure 8-2](#), shows a functional block diagram of a typical channel.

### 8.2 Functional Block Diagram



**Figure 8-1. Conceptual Block Diagram of a Digital Capacitive Isolator**



**8-2. Conceptual Block Diagram of a Digital Capacitive Isolator**

## 8.3 Feature Description

### 8.3.1 Refresh

The ISO7021 uses an edge based encoding scheme to transfer an input signal change across the isolation barrier versus sending across the DC state. The built in refresh function consistently validates that the DC output state of each isolator channel matches the DC input state. An internal watchdog timer monitors for activity on the individual inputs and transmits the logic state when there is no input signal transition for more than 100  $\mu$ s. This ensures that the input and output state of the isolator always match.

### 8.3.2 Electromagnetic Compatibility (EMC) Considerations

Many applications in harsh industrial environment are sensitive to disturbances such as electrostatic discharge (ESD), electrical fast transient (EFT), surge and electromagnetic emissions. These electromagnetic disturbances are regulated by international standards such as IEC 61000-4-x and CISPR 22. Although system-level performance and reliability depends, to a large extent, on the application board design and layout, the ISO70xx family of devices incorporates many chip-level design improvements for overall system robustness. Some of these improvements include:

- Robust ESD protection cells for input and output signal pins and inter-chip bond pads.
- Low-resistance connectivity of ESD cells to supply and ground pins.
- Enhanced performance of high voltage isolation capacitor for better tolerance of ESD, EFT and surge events.
- Bigger on-chip decoupling capacitors to bypass undesirable high energy signals through a low impedance path.
- PMOS and NMOS devices isolated from each other by using guard rings to avoid triggering of parasitic SCRs.
- Reduced common mode currents across the isolation barrier by ensuring purely differential internal operation.

The device has no issue being able to meet either CISPR 22 Class A and CISPR22 Class B standards in an unshielded environment.



## 8.4 Device Functional Modes

表 8-1 shows the functional modes for the device.

表 8-1. Function Table

$V_{CCI}$ <sup>1</sup>	$V_{CCO}$	INPUT (INx) <sup>3</sup>	OUTPUT (OUTx)	COMMENTS
PU	PU	H	H	Normal Operation: A channel output assumes the logic state of its input.
		L	L	
		X	Default	The channel output assumes the selected default option.
PD	PU	X	Default	When $V_{CCI}$ is unpowered, a channel output assumes the logic state based on the selected default option. Default is <i>High</i> for the device without the F suffix and <i>Low</i> for device with the F suffix. When $V_{CCI}$ transitions from unpowered to powered-up, a channel output assumes the logic state of the input. When $V_{CCI}$ transitions from powered-up to unpowered, channel output assumes the selected default state.
X	PD	X	Undetermined	When $V_{CCO}$ is unpowered, a channel output is undetermined and tri state <sup>2</sup> . When $V_{CCO}$ transitions from unpowered to powered-up, a channel output assumes the selected default option.

- $V_{CCI}$  = Input-side  $V_{CC}$ ;  $V_{CCO}$  = Output-side  $V_{CC}$ ; PU = Powered up ( $V_{CC} \geq 1.54$  V); PD = Powered down ( $V_{CC} \leq 1.54$  V); X = Irrelevant; H = High level; L = Low level ; Z = High Impedance.
- The outputs are in undetermined state when  $1.54$  V <  $V_{CCI}$ ,  $V_{CCO}$  <  $1.54$  V.
- A strongly driven input signal can weakly power the floating  $V_{CC}$  through an internal protection diode and cause undetermined output.

### 8.4.1 Device I/O Schematics

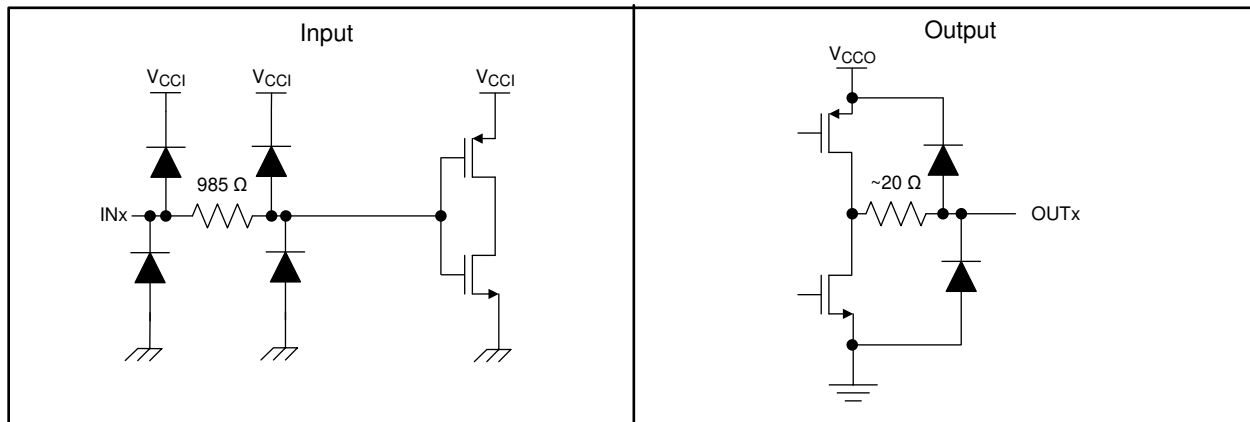


图 8-3. Device I/O Schematics

## 9 Application and Implementation

### 注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

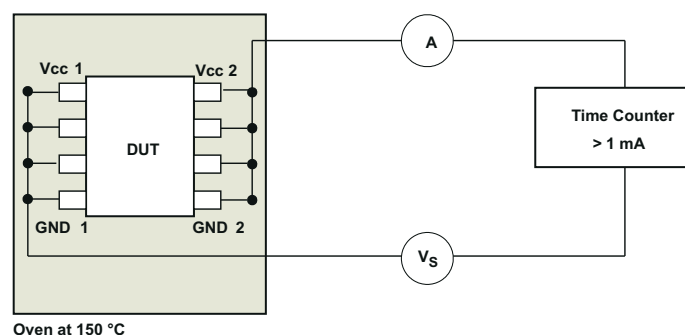
### 9.1 Application Information

The ISO7021 device is an ultra-low power digital isolator. The device uses single-ended CMOS-logic switching technology. The voltage range is from 1.71 V to 1.89 V and 2.25 V to 5.5 V for both supplies,  $V_{CC1}$  and  $V_{CC2}$ , and can be set irrespective of one another. When designing with digital isolators, keep in mind that because of the single-ended design structure, digital isolators do not conform to any specific interface standard and are only intended for isolating single-ended CMOS or TTL digital signal lines. The isolator is typically placed between the data controller (that is,  $\mu$ C or UART), and a data converter or a line transceiver, regardless of the interface type or standard. See [Isolated power and data interface for low-power applications reference design TI Design](#) for detailed information on designing the ISO70xx in low-power applications.

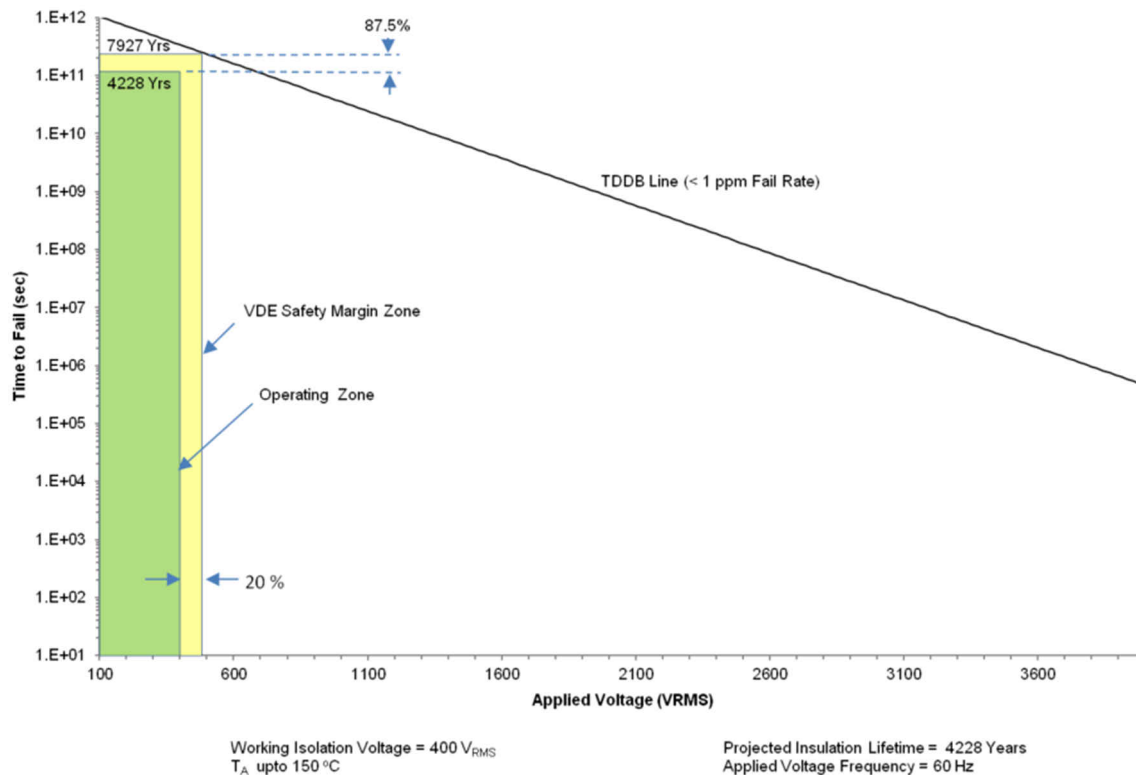
#### 9.1.1 Insulation Lifetime

Insulation lifetime projection data is collected by using industry-standard Time Dependent Dielectric Breakdown (TDDB) test method. In this test, all pins on each side of the barrier are tied together creating a two-terminal device and high voltage applied between the two sides; see [Figure 9-1](#) for TDDB test setup. The insulation breakdown data is collected at various high voltages switching at 60 Hz over temperature. For reinforced insulation, VDE standard requires the use of TDDB projection line with failure rate of less than 1 part per million (ppm) and a minimum insulation lifetime of 20 years. VDE standard also requires additional safety margin of 20% for working voltage and 87.5% for insulation lifetime which translates into minimum required life time of 37.5 years.

[Figure 9-2](#) shows the intrinsic capability of the isolation barrier to withstand high voltage stress over its lifetime. Based on the TDDB data, the intrinsic capability of these devices is 400 VRMS with a lifetime of >100 years. Other factors, such as package size, pollution degree, material group, and so forth can further limit the working voltage of the component. The working voltage of the DBQ-16 package specified up to 400 VRMS. At the lower working voltages, the corresponding insulation barrier life time is much longer.



**Figure 9-1. Test Setup for Insulation Lifetime Measurement**



✎ 9-2. Insulation Lifetime Projection Data

### 9.1.2 Intrinsic Safety

The ISO7021 supports Intrinsically Safe (IS) to IS applications and carry IECEx and ATEX certifications. These devices do not currently support IS to non-IS galvanic isolation applications due to the minimum insulation thickness requirements of IEC 60079-11.

#### 9.1.2.1 Schedule of Limitations

These components are certified to comply with IEC 60079-0, Edition 7, IEC 60079-11, Edition 6, EN IEC60079-0:2018 and EN 60070-11:2012. When one of these components is used in an equipment, the component is to be soldered on a PCB inside a suitable enclosure and re-evaluated as an equipment. The operating temperature range of these components is -55°C to +85°C. The creepage and clearance distances across the isolating component have been evaluated, but the distance to other circuitry remain the responsibility of the user of the final equipment.

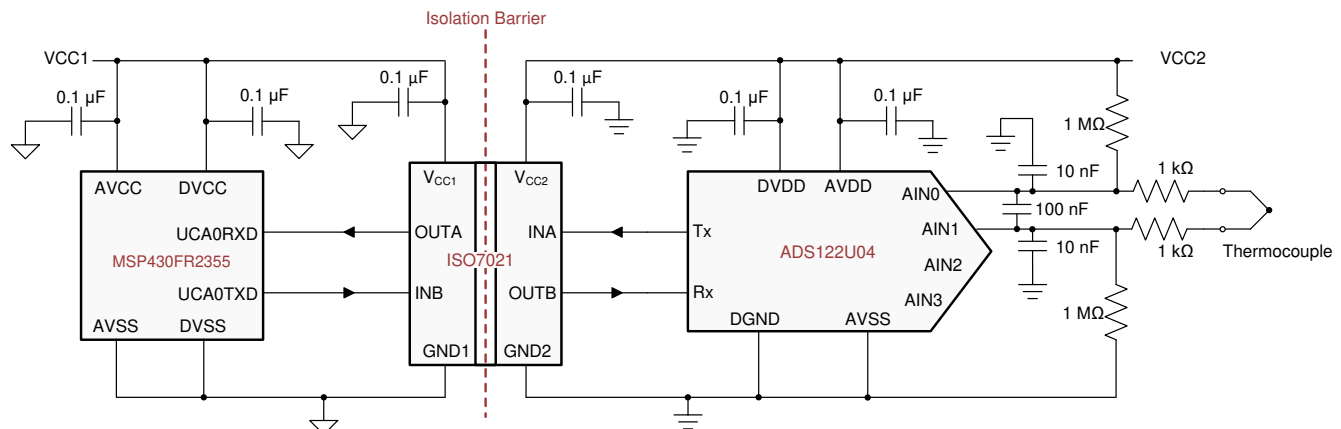
This assembly is an isolating component between separate intrinsically safe circuits. The assembly must be connected to suitably certified intrinsically safe circuits considering the entity parameters and temperature ratings in the application scenario shown in 表 9-1

**表 9-1. Entity Parameters and Temperature Ratings**

APPLICATION	ENTITY PARAMETERS SIDE 1	ENTITY PARAMETERS SIDE 2	AMBIENT TEMPERATURE RANGE	MAXIMUM COMPONENT TEMPERATURE
IS to IS: Case 1	Ui = 50 V	Ui = 50 V	-55°C to +85°C	183°C
	Ii = 300 mA	Ii = 300 mA		
	Pi = 1.3 W	Pi = 1.3 W		
	Li = 0 H	Li = 0 H		
	Ci = 4 pF	Ci = 4 pF		

## 9.2 Typical Application

 **9-3** shows the isolated UART.



### 9-3. Isolated UART for a Temperature Field Transmitter

## 9.2.1 Design Requirements

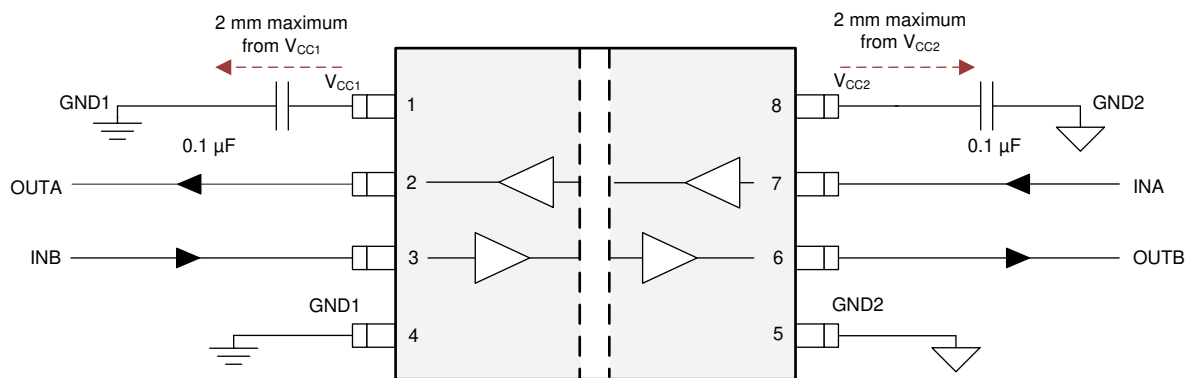
To design with these devices, use the parameters listed in 表 9-2.

**表 9-2. Design Parameters**

PARAMETER	VALUE
Supply voltage, $V_{CC1}$ and $V_{CC2}$	1.71 V to 1.89 V or 2.25 V to 5.5 V
Decoupling capacitor between $V_{CC1}$ and GND1	0.1 $\mu$ F
Decoupling capacitor from $V_{CC2}$ and GND2	0.1 $\mu$ F

## 9.2.2 Detailed Design Procedure

Unlike optocouplers, which require external components to improve performance, provide bias, or limit current, the device only require two external bypass capacitors to operate.



**図 9-4. Typical ISO7021 Circuit Hook-up**

### 9.2.3 Application Curves

The following typical eye diagrams of the device indicates wide open eye at the maximum data rate of 4 Mbps.

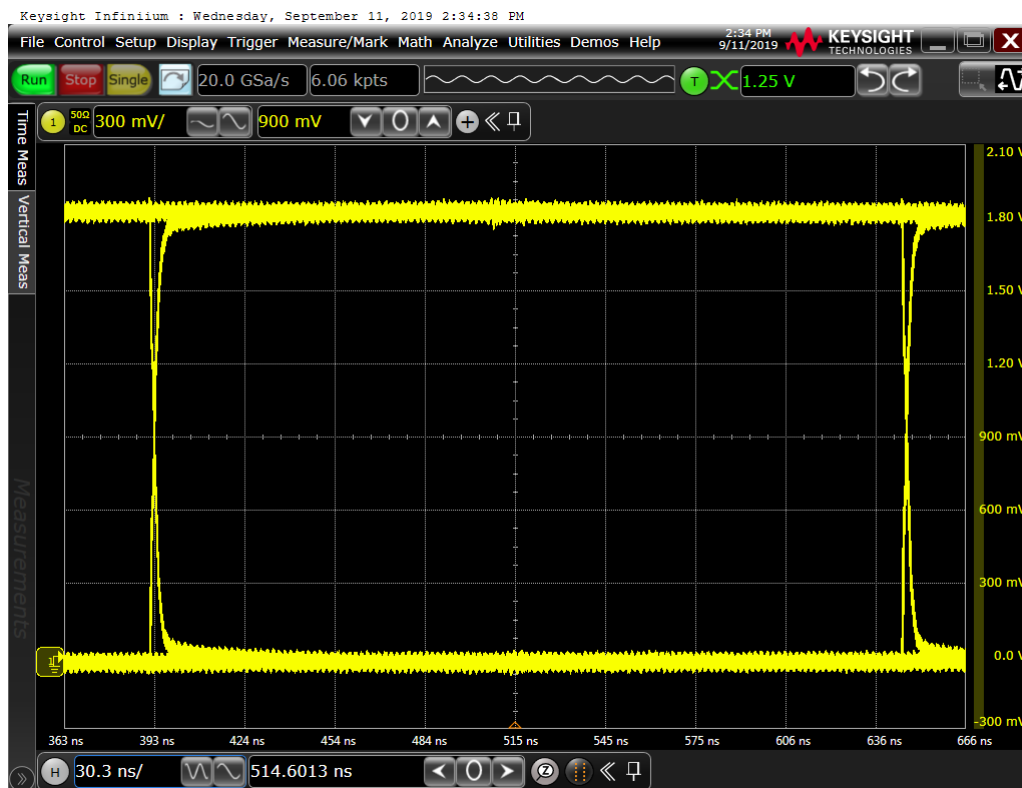


图 9-5. Eye Diagram at 4 Mbps PRBS  $2^{16} - 1$ , 1.8 V and 25°C

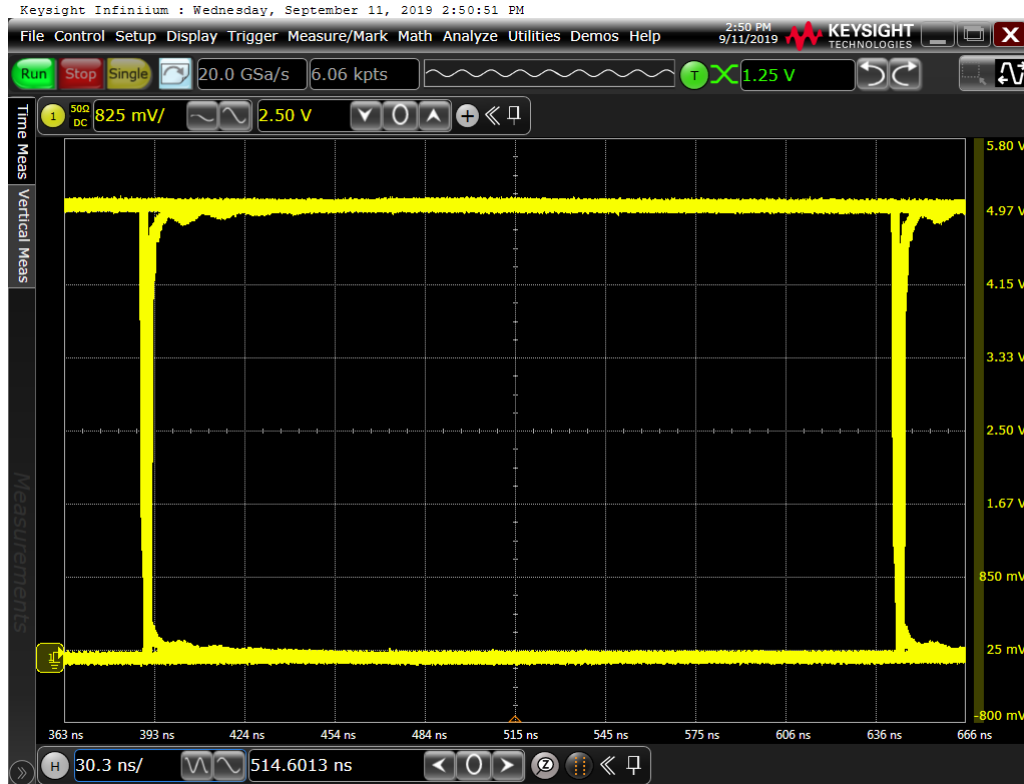


Figure 9-6. Eye Diagram at 4 Mbps PRBS 2<sup>16</sup> – 1, 5 V and 25°C

## 10 Power Supply Recommendations

Put a 0.1-μF bypass capacitor at the input and output supply pins (V<sub>CC1</sub> and V<sub>CC2</sub>) to make sure that operation is reliable at data rates and supply voltage. Put the capacitors as near to the supply pins as possible. If only one primary-side power supply is available in an application, use a transformer driver to help generate the isolated power for the secondary-side. Texas Instruments recommends the [SN6501](#) device or [SN6505A](#) device. Refer to the [SN6501 Transformer Driver for Isolated Power Supplies data sheet](#) or [SN6505 Low-Noise 1-A Transformer Drivers for Isolated Power Supplies data sheet](#) for detailed power supply design and transformer selection recommendations.

## 11 Layout

### 11.1 Layout Guidelines

A minimum of four layers is required to accomplish a low EMI PCB design (see [Figure 11-1](#)). Layer stacking should be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane and low-frequency signal layer.

- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100 pF/in<sup>2</sup>.
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.

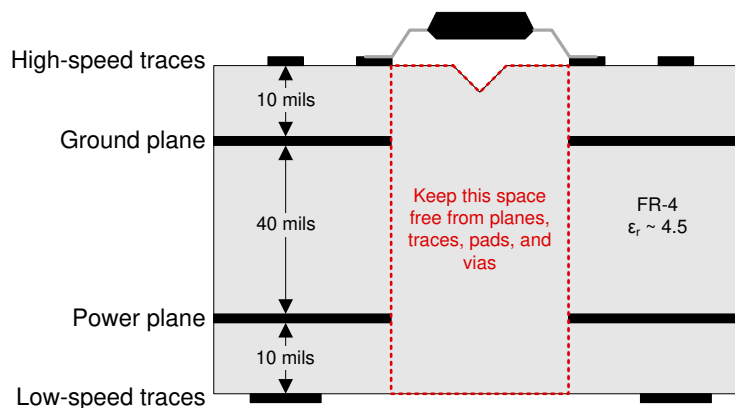
If an additional supply voltage plane or signal layer is needed, add a second power or ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

Refer to the [Digital Isolator Design Guide](#) for detailed layout recommendations.

#### 11.1.1 PCB Material

For digital circuit boards operating at less than 150 Mbps, (or rise and fall times greater than 1 ns), and trace lengths of up to 10 inches, use standard FR-4 UL94V-0 printed circuit board. This PCB is preferred over cheaper alternatives because of lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and the self-extinguishing flammability-characteristics.

### 11.2 Layout Example



**Figure 11-1. Recommended Layer Stack**



## 12 Device and Documentation Support

### 12.1 Documentation Support

#### 12.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [Digital Isolator Design Guide](#)
- Texas Instruments, [Isolation Glossary](#)
- Texas Instruments, [ADS1220 4-Channel, 2-kSPS, Low-Power, 24-Bit ADC with Integrated PGA and Reference data sheet](#)
- Texas Instruments, [ADS122U04 24-Bit, 4-Channel, 2-kSPS, Delta-Sigma ADC With UART Interface data sheet](#)
- Texas Instruments, [ADS124S0x Low-Power, Low-Noise, Highly Integrated, 6- and 12-Channel, 4-kSPS, 24-Bit, Delta-Sigma ADC with PGA and Voltage Reference data sheet](#)
- Texas Instruments, [Uniquely Efficient Isolated DC/DC Converter for Ultra-Low Power and Low-Power Applications TI Design](#)
- Texas Instruments, [SN6501 Transformer Driver for Isolated Power Supplies data sheet](#)
- Texas Instruments, [SN6505A Low-Noise 1-A Transformer Drivers for Isolated Power Supplies data sheet](#)
- Texas Instruments, [Isolated power and data interface for low-power applications reference design TI Design](#)

### 12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

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### 12.6 用語集

[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ISO7021D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7021	<a href="#">Samples</a>
ISO7021DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7021	<a href="#">Samples</a>
ISO7021FD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7021F	<a href="#">Samples</a>
ISO7021FDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	7021F	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## TAPE AND REEL INFORMATION



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7021DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7021FDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7021DR	SOIC	D	8	2500	350.0	350.0	43.0
ISO7021FDR	SOIC	D	8	2500	367.0	367.0	38.0

## TUBE



\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
ISO7021D	D	SOIC	8	75	505.46	6.76	3810	4
ISO7021FD	D	SOIC	8	75	505.46	6.76	3810	4



**D0008A**

# PACKAGE OUTLINE

**SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

## NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

# EXAMPLE BOARD LAYOUT

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



## EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE  
BASED ON .005 INCH [0.125 MM] THICK STENCIL  
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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